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IN THE UNITED STATES PATENT AND TRADE MARKS OFFICE

Applicant: R.C. Foss et al

Serial No: 07/680,747

Filed: April 5, 1991

Title: METHOD FOR DRAM SENSING CURRENT CONTROL

Art Unit: 2502

RECEIVED

Examiner: T. Dinh

OCT 20 1993

Our File: 628.30050X00

GROUP 2400

The Commissioner of Patents
and Trade Marks,
Washington, D.C., 20231
U.S.A.

October 18, 1993

Dear Sir:

This is in response to the official action dated May 17th, 1993 in the above-identified application.

Please amend the claims as follows:

1. (Amended) A dynamic random access memory (DRAM) comprising:

(a) a plurality of bit storage capacitors,

(b) a folded bit line comprised of a complementary bit line pair for receiving charge stored on one of said capacitors, having bit line capacitance,

(c) a sense amplifier having a pair of sense nodes for sensing a voltage differential across said sense nodes,

(d) high resistance controllable current leakage imperfect isolating means connecting said bit line to said